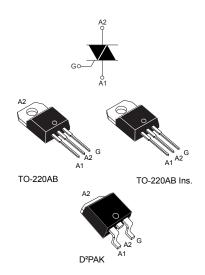


# 10 A Snubberless™, logic level and standard Triacs



#### **Features**

- · Medium current Triac
- · Low thermal resistance with clip bonding
- · Low thermal resistance insulation ceramic for insulated BTA
- High commutation (4Q) or very high commutation (3Q, Snubberless™) capability
- BTA series UL1557 certified (file ref: 81734)
- Packages are RoHS (2002/95/EC) compliant

#### **Description**

Available either in through-hole or surface mount packages, the BTA10, BTB10 and T10xx Triac series are suitable for general purpose mains power AC switching. They can be used as ON/OFF function in applications such as static relays, heating regulation or induction motor starting circuit. They are also recommended for phase control operations in light dimmers and appliance motors speed controllers.

The Snubberless™ versions (W suffix and T10xx) are especially recommended for use on inductive loads, because of their high commutation performance. By using an internal ceramic pad, the Snubberless™ series provide an insulated tab (rated at 2500 V<sub>RMS</sub>) complying with UL standards (file reference: E81734).

Product status link	
BTA10, BTB10, T1035, T1050	

Product summary							
I <sub>T(RMS)</sub> 10 A							
$V_{DRM}/V_{RRM}$	600 and 800 V						
I <sub>GT</sub>	25 to 50 mA						



# 1 Characteristics

Table 1. Absolute maximum ratings

Symbol	Parameters	Value	Unit		
<b>I</b>	DMS on state current (full sine ways)	TO-220AB	T <sub>c</sub> = 105 °C	10	A
I <sub>T(RMS)</sub>	RMS on-state current (full sine wave)	TO-220AB Ins.	T <sub>c</sub> = 95 °C	10	^
l	Non repetitive surge peak on-state current (full cycle, T <sub>i</sub>	F = 50 Hz	t <sub>p</sub> = 20 ms	100	A
I <sub>TSM</sub>	initial = 25 °C)	F = 60 Hz	t <sub>p</sub> = 16.7 ms	105	
I <sup>2</sup> t	I <sup>2</sup> t value for fusing	55	A <sup>2</sup> s		
dl/dt	Critical rate of rise of on-state current	F = 120 Hz	T <sub>i</sub> = 125 °C	50	A/µs
	$I_G = 2 \times I_{GT}$ , $t_r \le 100 \text{ ns}$		,		L'
V <sub>DSM</sub> /V <sub>RSM</sub>	Non repetitive surge peak off-state voltage	t <sub>p</sub> = 10 ms	T <sub>j</sub> = 25 °C	V <sub>DRM</sub> /V <sub>RRM</sub> + 100	V
I <sub>GM</sub>	Peak gate current	t <sub>p</sub> = 20 μs	T <sub>j</sub> = 125 °C	4	Α
P <sub>G(AV)</sub>	Average gate power dissipation		T <sub>j</sub> = 125 °C	1	W
T <sub>stg</sub>	Storage junction temperature range	-40 to +150	°C		
Tj	Operating junction temperature range			-40 to +125	°C

Table 2. Static electrical characteristics

Symbol	Test conditions	Tj		Value	Unit
V <sub>T</sub> <sup>(1)</sup>	I <sub>TM</sub> = 14 A, t <sub>p</sub> = 380 μs	25 °C	Max.	1.55	V
V <sub>TO</sub>	threshold on-state voltage	125 °C	Max.	0.85	V
R <sub>D</sub>	Dynamic resistance	125 °C	Max.	40	mΩ
I <sub>DRM</sub> /I <sub>RRM</sub>	V <sub>DRM</sub> = V <sub>RRM</sub>	25 °C	Max.	5	μA
	VDRM - VRRM	125 °C	ividX.	1	mA

<sup>1.</sup> For both polarities of A2 referenced to A1

Table 3. Electrical characteristics ( $T_j$  = 25 °C, unless otherwise specified) - Snubberless<sup>™</sup> (3 quadrants)

Symbol	Parameters	Quadrant		T1035	BTA10-xCW BTB10-xCW	T1050 BTA10-xBW BTB10-xBW	Unit
I <sub>GT</sub>	$V_D = 12 \text{ V, R}_L = 33 \Omega$	1 - 11 - 111	Max.	3	5	50	mA
V <sub>GT</sub>	VD = 12 V, IVL = 33 12	1 - 11 - 111	Max.		1.3		V
$V_{GD}$	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega, T_j = 125 \text{ °C}$	1 - 11 - 111	Min.		0.2		V
I <sub>H</sub>	I <sub>T</sub> = 500 mA	1 - 11 - 111	Max.	3	5	50	mA
IL	I <sub>G</sub> = 1.2 I <sub>GT</sub>	1 - 111	Max.	5	60	70	mA
'L	1G - 1.2 1G1	II	Max.	80	60	80	IIIA
dV/dt <sup>(2)</sup>	$V_D$ = 67 % $V_{DRM}$ gate open, $T_j$ = 125 °C		Min.	500		1000	V/µs

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Symbol	Parameters	Quadrant		T1035	BTA10-xCW BTB10-xCW	T1050 BTA10-xBW BTB10-xBW	Unit
(dl/dt)c <sup>(2)</sup>	Without snubber, $T_j = 125$ °C		Min.	5	.5	9	A/ms

- 1. Minimum  $I_{GT}$  is guaranteed at 5 % of  $I_{GT}$  max.
- 2. For both polarities of A2 referenced to A1

Table 4. Electrical characteristics ( $T_j$  = 25 °C, unless otherwise specified) - standard Triac (4 quadrants)

Symbol	Parameters	Quadrant		Va	lue	Unit
Syllibol	Faidifieters	Quaurant		С	В	Offic
I <sub>GT</sub> <sup>(1)</sup>		1 - 11 - 111	Max.	25	50	mA
iGT.	$V_D = 12 \text{ V}, R_L = 33 \Omega$	IV	Max.	50	100	IIIA
V <sub>GT</sub>		All	Max.	1	.3	V
$V_{GD}$	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega, T_j = 125 \text{ °C}$	1 - 11 - 111	Min.	0	.2	V
IH <sup>(2)</sup>	I <sub>T</sub> = 500 mA	1 - 11 - 111	Max.	25	50	mA
IL	I <sub>G</sub> = 1.2 I <sub>GT</sub>	1 - 111	Max.	40	50	m A
".	IG = 1.2 IG	II	Max.	80	100	mA
dV/dt <sup>(2)</sup>	V <sub>D</sub> = 67 % V <sub>DRM</sub> gate open, T <sub>j</sub> = 125 °C		Min.	200	400	V/µs
(dV/dt)c <sup>(2)</sup>	(dl/dt)c = 4.4 A/ms, T <sub>j</sub> = 125 °C		Min.	5	10	V/µs

- 1. Minimum  $I_{GT}$  is guaranteed at 5 % of  $I_{GT}$  max.
- 2. For both polarities of A2 referenced to A1

Table 5. Thermal resistance

Symbol	Paramete	Value	Unit	
Pour (typ.)	Junction to case (AC)	TO-220AB / D <sup>2</sup> PAK	1.5	
$R_{th(j-c)}$ (typ.)	Junction to case (AC)	TO-220AB insulated	2.4	°C/W
P., (may )	Junction to ambient (S <sup>(1)</sup> = 2 cm <sup>2</sup> )	D²PAK	45	C/VV
R <sub>th(j-a)</sub> (max.)	Junction to ambient	TO-220AB / TO-220AB ins	60	

1. Copper surface under tab.



### 1.1 Characteristics (curves)

Figure 2. Maximum power dissipation versus on-state RMS current (full cycle)

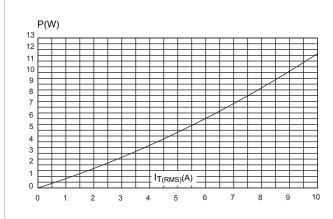


Figure 3. RMS on-state current versus case temperature (full cycle)

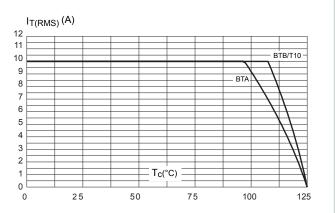


Figure 4. Relative variation of thermal impedance versus pulse duration

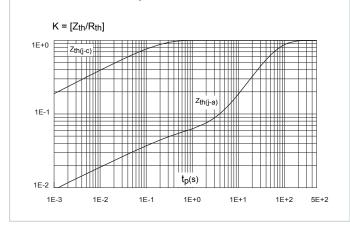


Figure 5. On-state characteristics (maximum values)

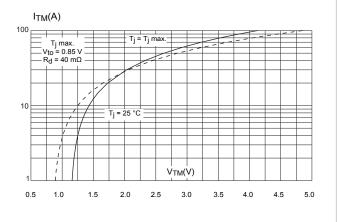


Figure 6. Surge peak on-state current versus number of cycles

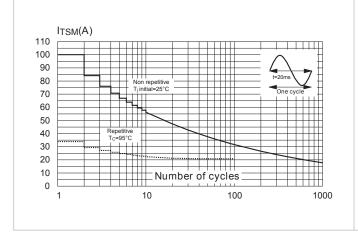
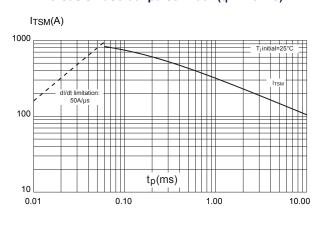


Figure 7. Non repetitive surge peak on-state current versus sinusoidal pulse width ( $t_P < 10 \text{ ms}$ )



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Figure 8. Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values)

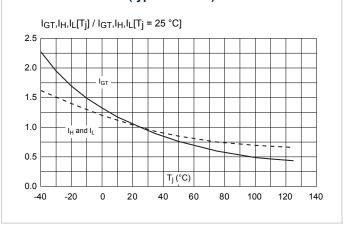


Figure 9. Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values)

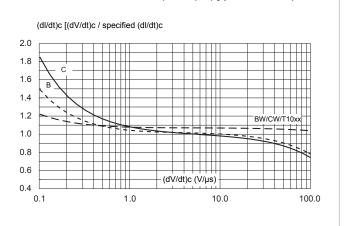


Figure 10. Relative variation of critical rate of decrease of main current versus junction temperature

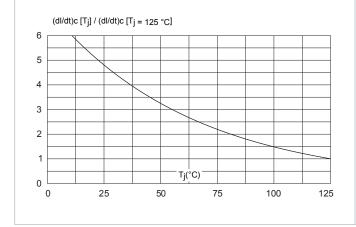
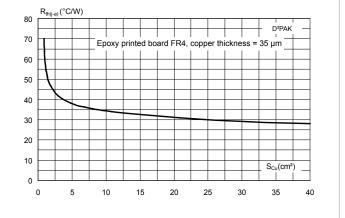


Figure 11. D<sup>2</sup>PAK thermal resistance junction to ambient versus copper surface under tab



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# 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

### 2.1 D<sup>2</sup>PAK package information

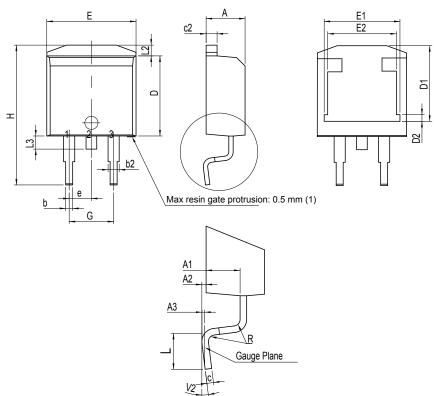


Figure 12. D<sup>2</sup>PAK package outline

(1) Resin gate is accepted in each of position shown on the drawing, or their symmetrical.

Table 6. D<sup>2</sup>PAK package mechanical data

				Dimensions					
Ref.	Millimeters			Millimeters Inches <sup>(1)</sup>					
	Min.	Тур.	Max.	Min.	Тур.	Max.			
Α	4.30		4.60	0.1693		0.1811			
A1	2.49		2.69	0.0980		0.1059			
A2	0.03		0.23	0.0012		0.0091			
A3		0.25			0.0098				
b	0.70		0.93	0.0276		0.0366			
b2	1.25		1.7	0.0492		0.0669			

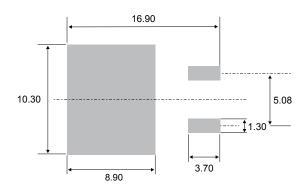
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	Dimensions								
Ref.		Millimeters			Inches <sup>(1)</sup>				
	Min.	Тур.	Max.	Min.	Тур.	Max.			
С	0.45		0.60	0.0177		0.0236			
c2	1.21		1.36	0.0476		0.0535			
D	8.95		9.35	0.3524		0.3681			
D1	7.50		8.00	0.2953		0.3150			
D2	1.30		1.70	0.0512		0.0669			
е	2.54			0.1					
Е	10.00		10.28	0.3937		0.4047			
E1	8.30		8.70	0.3268		0.3425			
E2	6.85		7.25	0.2697		0.2854			
G	4.88		5.28	0.1921		0.2079			
Н	15		15.85	0.5906		0.6240			
L	1.78		2.28	0.0701		0.0898			
L2	1.27		1.40	0.0500		0.0551			
L3	1.40		1.75	0.0551		0.0689			
R		0.40			0.0157				
V2	0°		8°	0°		8°			

<sup>1.</sup> Dimensions in inches are given for reference only

Figure 13. D<sup>2</sup>PAK recommended footprint (dimensions are in mm)





## 2.2 TO-220AB non ins. and insulated package information

С В b2 Resin gate 0.5 mm max. protusion<sup>(1)</sup> Α 14 13 c2 a1 12 a2 Μ c1 Resin gate 0.5 mm b1 max. protusion<sup>(1)</sup>

Figure 14. TO-220AB non ins. and insulated package outline

(1)Resin gate position accepted in one of the two positions or in the symmetrical opposites.

Table 7. TO-220AB non ins. and insulated package mechanical data

	Dimensions							
Ref.		Millimeters			Inches1			
	Min.	Тур.	Max.	Min.	Тур.	Max.		
Α	15.20		15.90	0.5984		0.6260		
a1		3.75			0.1476			
a2	13.00		14.00	0.5118		0.5512		
В	10.00		10.40	0.3937		0.4094		
b1	0.61		0.88	0.0240		0.0346		
b2	1.23		1.32	0.0484		0.0520		
С	4.40		4.60	0.1732		0.1811		

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	Dimensions							
Ref.		Millimeters		Inches1				
	Min.	Тур.	Max.	Min.	Тур.	Max.		
c1	0.49		0.70	0.0193		0.0276		
c2	2.40		2.72	0.0945		0.1071		
е	2.40		2.70	0.0945		0.1063		
F	6.20		6.60	0.2441		0.2598		
ı	3.73		3.88	0.1469		0.1528		
L	2.65		2.95	0.1043		0.1161		
12	1.14		1.70	0.0449		0.0669		
13	1.14		1.70	0.0449		0.0669		
14	15.80	16.40	16.80	0.6220	0.6457	0.6614		
М		2.6			0.1024			

<sup>1.</sup> Inch dimensions are for reference only.

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# 3 Ordering information

Figure 15. BTA10 and BTB10 series ordering information scheme

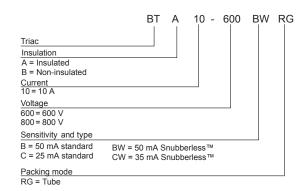
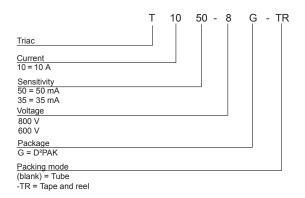


Figure 16. T10xx series ordering information scheme



**Table 8. Ordering information** 

Order code	Marking	Package	Weight	Base qty.	Delivery mode
BTA10-600BRG	BTA10-600B	TO-220AB Ins.	2.3 g	50	Tube
BTA10-600CRG	BTA10-600C				
BTA10-600BWRG	BTA10-600BW				
BTA10-600CWRG	BTA10-600CW				
BTA10-800BWRG	BTA10-800BW				
BTA10-800CWRG	BTA10-800CW				
BTB10-600BWRG	BTB10-600BW	TO-220AB			
BTB10-800BWRG	BTB10-800BW				
T1035-6G	T1035-6G	D²PAK	1.50 g		
T1050-8G	T1050-8G				
T1035-6G-TR	T1035-6G			1000	Tape and reel 13"
T1050-8G-TR	T1050-8G				

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# **Revision history**

Table 9. Document revision history

Date	Revision	Changes
Sep-2002	5A	Last update.
13-Feb-2006	6	TO-220AB delivery mode changed from bulk to tube. ECOPACK statement added.
06-Feb-2017	7	Added D²PAK package information.
15-Mar-2018	8	Updated Table 3. Electrical characteristics (Tj = 25 °C, unless otherwise specified) - Snubberless™ (3 quadrants), Section 3 Ordering information and Section 2.1 D²PAK package information.  Added RPNs T1035 and T1050.
01-Mar-2019	9	Updated Links syntax.



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